

ABSTRACT OF THE DISCLOSURE

A method for forming a capacitor insulation film having a high dielectric constant includes the steps of depositing an amorphous strontium titanate film on a bottom electrode, forming
5 a top electrode on the strontium titanate film and heat treating the strontium titanate film at a temperature between 500 degrees C and 650 degrees C in an inert gas ambient to crystallize the amorphous strontium titanate film.